/ Descriptions

TO-220FL N MOS N-CHANNEL MOSFET in a TO-220FL Plastic Package.

/ Features

, ,

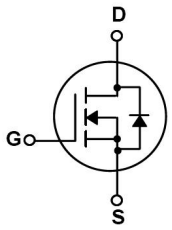
Low gate charge, Low Crss , Fast switching.

/ Applications

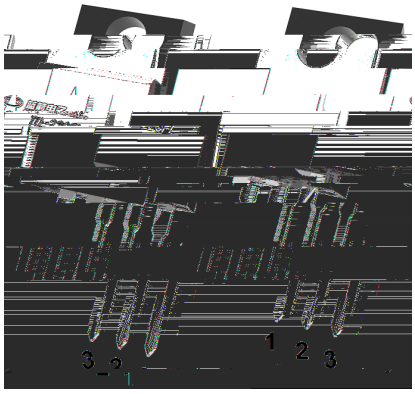
UPS

High efficiency switch mode power supplies, Electronic lamp ballasts based on half bridge, UPS .

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S

/ Marking

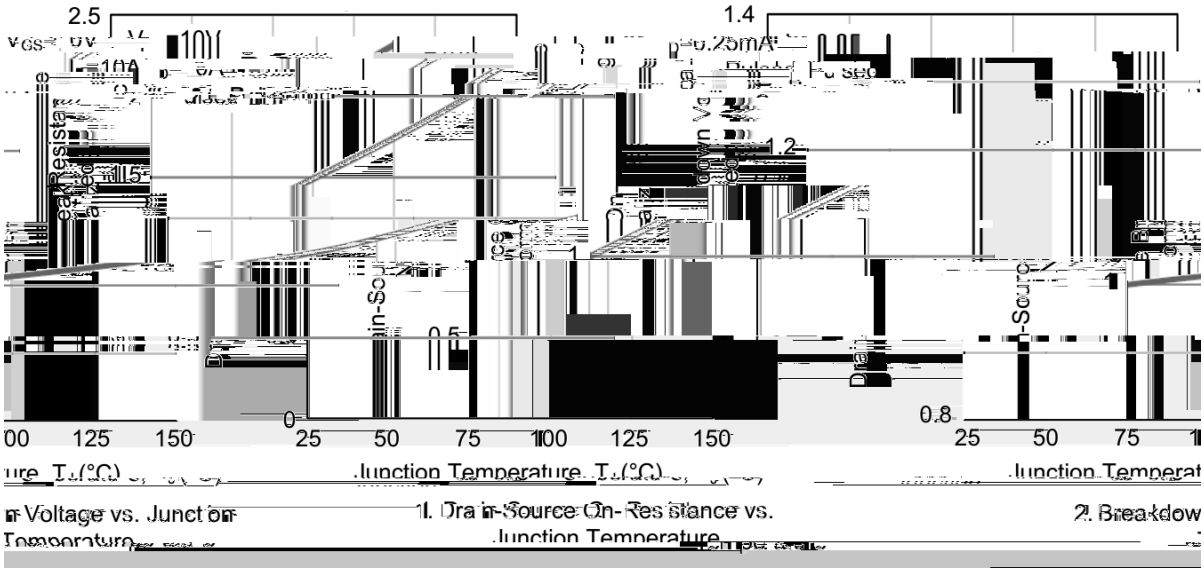
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	I_D(Tc=25)	20	A
Drain Current - Pulsed	I_{DM}	40	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	1 4810(E)]TJ7.0282)-73(R/TTc0	372

0e,799340Junction 0 Cas 0

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit 08SbÉXeqÐ¿SS

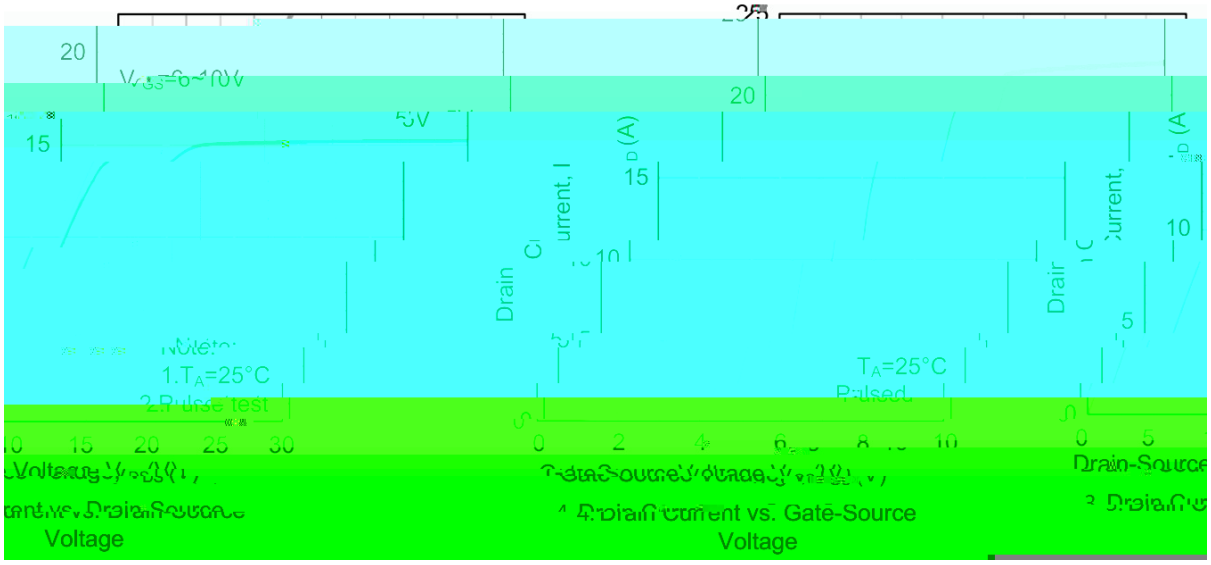
/ Electrical Characteristic Curve



Voltage vs. Junction Temperature

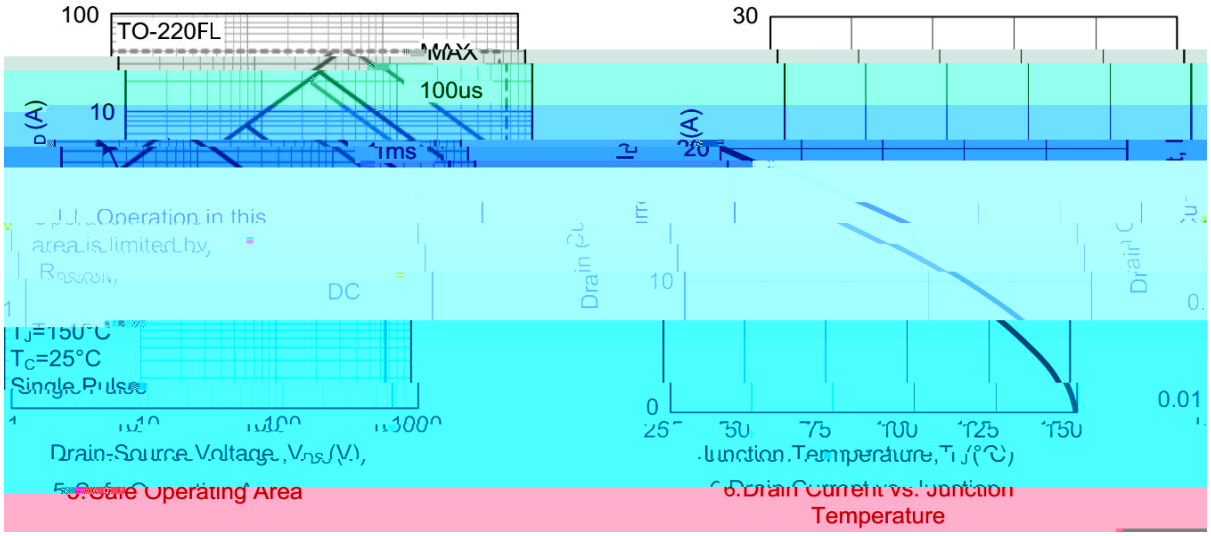
1. Drain-Source On-Resistance vs. Junction Temperature

2. Breakdow



Voltage

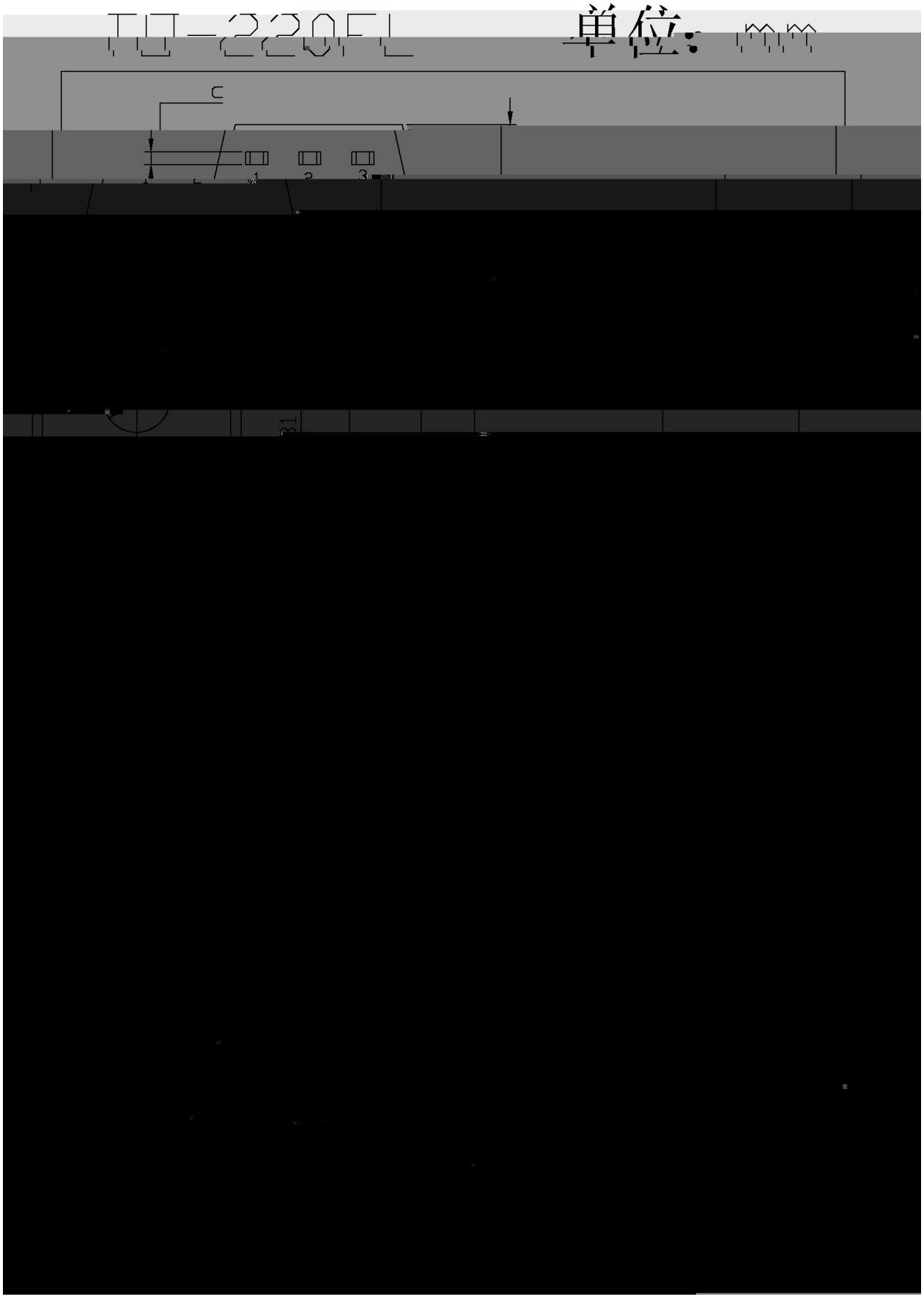
4. Drain Current vs. Gate-Source Voltage



Safe Operating Area

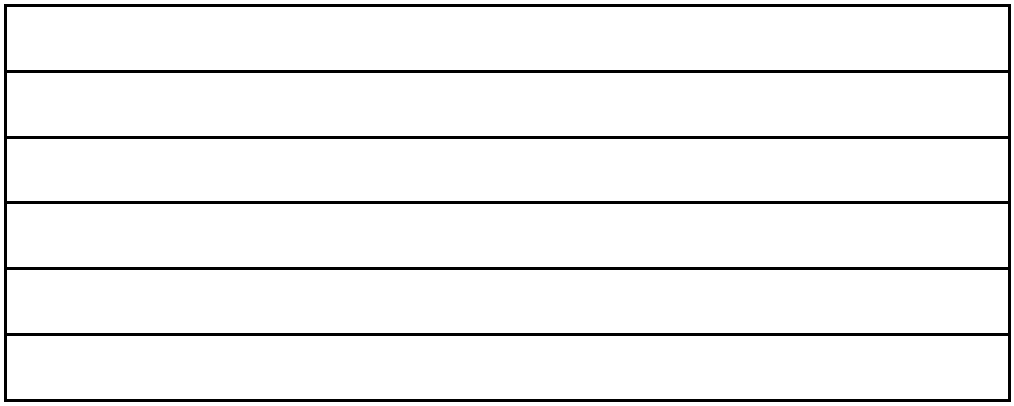
6.Drain Current vs. Junction Temperature

/ Package Dimensions



BRFL20N65

( ) / Temperature Profile for Dip Soldering(Pb-Free)



Note:

1 25 150 60 90sec;

2 255±5 5±0.5sec;

3 2 10 /sec.

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ TUBE